Abstracts

A GaAs MESFET transient model capable of predicting trap-induced memory effects under complex digital modulation

F. Wang, W.D. Jemison and J.C.M. Hwang. "A GaAs MESFET transient model capable of predicting trap-induced memory effects under complex digital modulation." 2001 MTT-S International Microwave Symposium Digest 01.2 (2001 Vol. II [MWSYM]): 815-818 vol.2.

A transient model for GaAs MESFETs is presented that can predict distortion of digitally modulated carrier waveforms due to memory effects induced by both low-frequency dispersion and gate-lag. Experimental and simulated results are presented which demonstrate, for the first time, the successful prediction of these effects for multilevel pulse modulated waveforms.

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